

### Abstract

A method and apparatus for forming a relatively thin releasable layer of copper on a carrier substrate. First, a separation facilitating layer is provided on the carrier substrate. A layer of vapor-deposited copper is then formed over the separation facilitating layer to protect the separation facilitating layer during subsequent processing. Thereafter, the thickness of the copper layer is increased by the electrodeposition of copper onto the vapor-deposited layer. The copper layer is applied to a dielectric and is released from the carrier substrate at the separation facilitating layer.